

## SL34A SCHOTTKY RECTIFIER

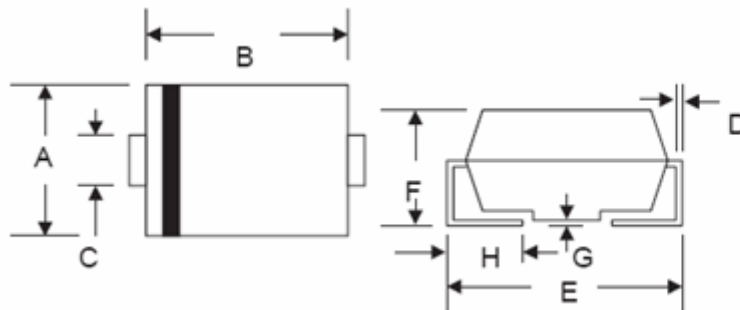
### Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Features:

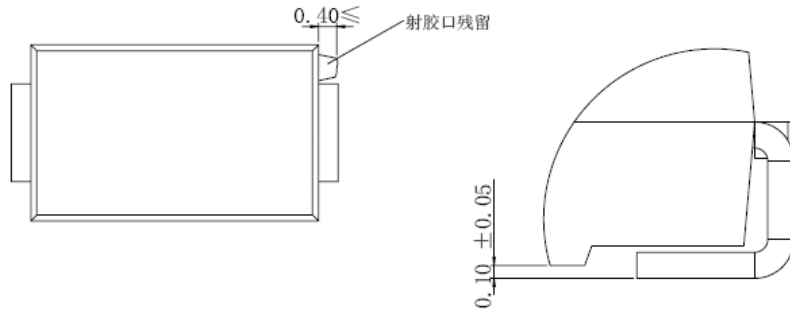
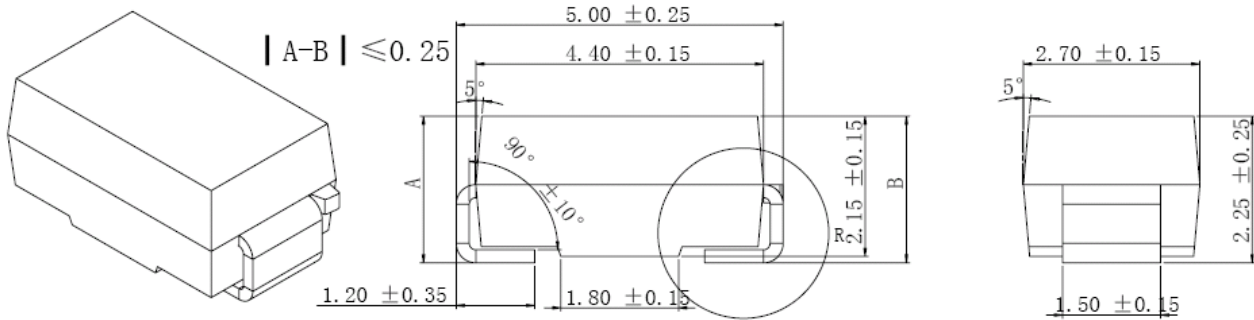
- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Mechanical Dimensions (In mm / Inches)



SMA/DO-214AC				
Dim	Min	Max	Min	Max
A	2.50	2.90	0.098	0.114
B	4.00	4.60	0.157	0.181
C	1.40	1.60	0.055	0.063
D	0.152	0.305	0.006	0.012
E	4.80	5.28	0.189	0.208
F	2.00	2.44	0.079	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060
	In mm		In inch	

### OPTION 1



**OPTION 2(JK)**

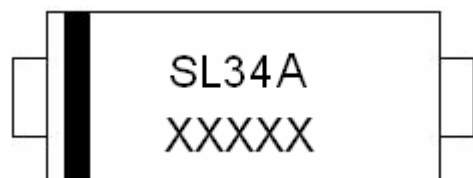
**SMA**



Technical Data  
Data Sheet N1345 Rev. -

**Green Products**

**Marking Diagram:**



Where XXXXX is YYWWL

- SL = Device Type
- 3 = Forward Current (3A)
- 4 = Reverse Voltage (40V)
- A = Package type
- YY = Year
- WW = Week
- L = Lot Number

**Cautions :** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
SL34A	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	40	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle ,rectangular wave form	3.0	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse	70	A



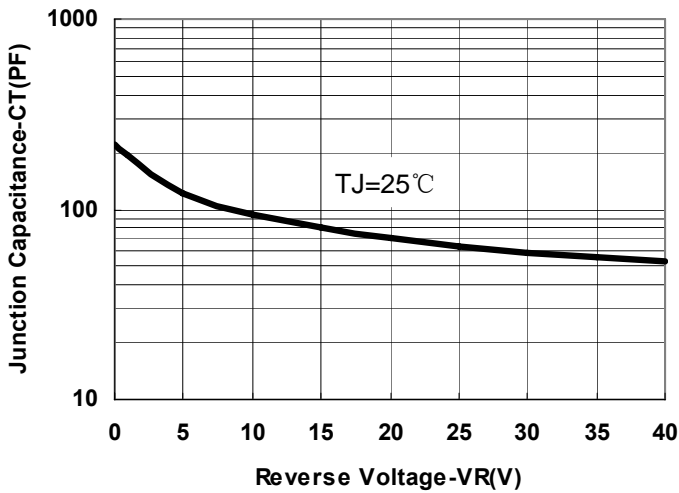
**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	$V_{F1}$	@ 3A, Pulse, $T_J = 25^\circ\text{C}$	0.50	V
	$V_{F2}$	@ 3A, Pulse, $T_J = 125^\circ\text{C}$	0.45	V
Reverse Current	$I_{R1}$	@ $V_R = \text{rated VR}$ $T_J = 25^\circ\text{C}$	1.0	mA
	$I_{R2}$	@ $V_R = \text{rated VR}$ $T_J = 125^\circ\text{C}$	55	mA
Junction Capacitance	$C_j$	@ $V_R = 5.0\text{ V}$ , $T_c = 25^\circ\text{C}$ $f_{\text{SIG}} = 1\text{MHz}$	250	pF

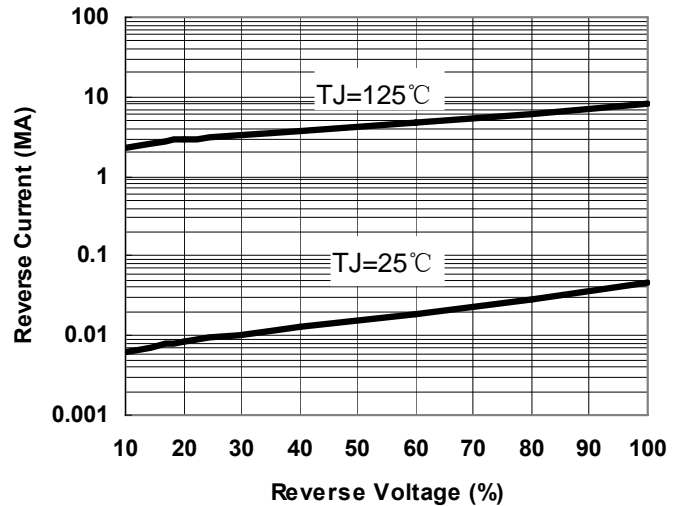
\* Pulse Width < 300 $\mu\text{s}$ , Duty Cycle <2%

**Thermal-Mechanical Specifications:**

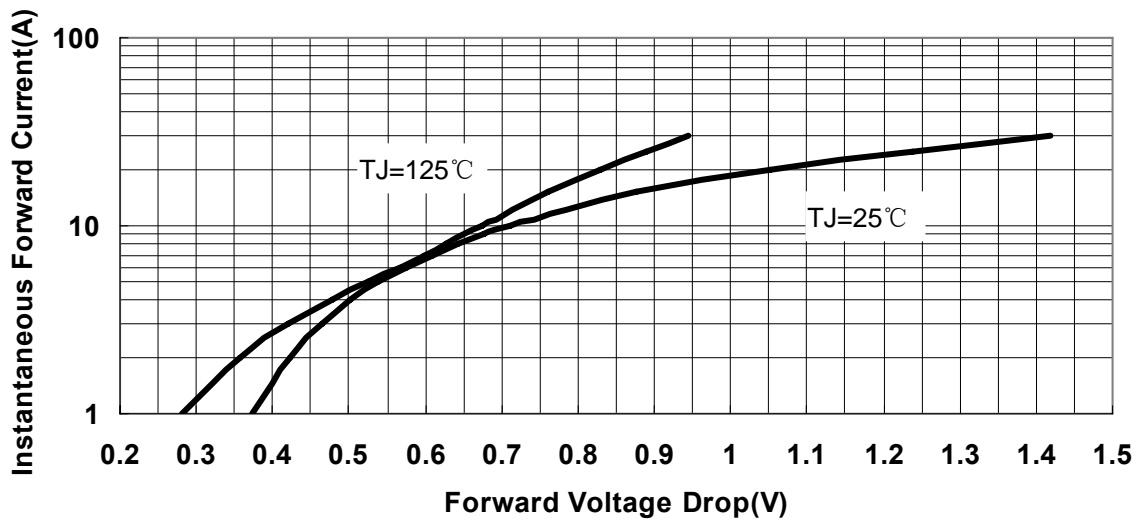
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +125	$^\circ\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +125	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	8	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.68	g
Case Style	SMB			



**Fig.1-Typical Junction Capacitance**



**Fig.2-Typical Reverse Characteristics**



**Fig.3-Typical Instantaneous Forward Voltage Characteristics**



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